

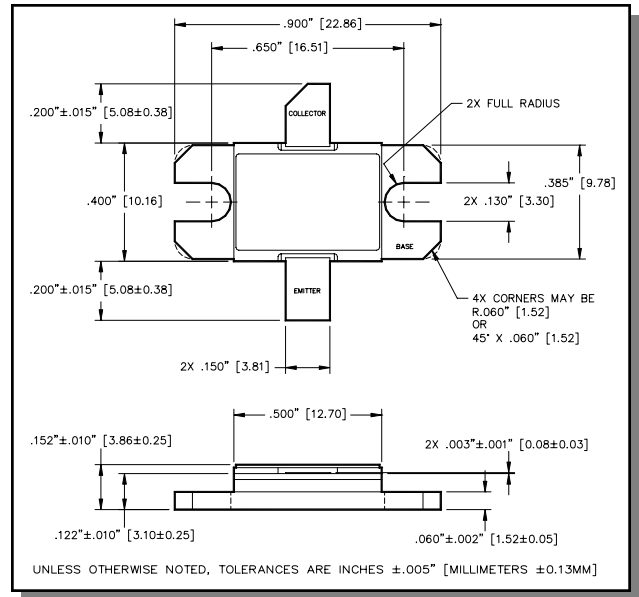
**Radar Pulsed Power Transistor**  
**100W, 1.1-1.3 GHz, 3μs Pulse, 30% Duty**

**M/A-COM Products**  
**Released, 30 May 07**

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	70	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	9.0	A
Power Dissipation @ +25°C	$P_{TOT}$	350	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient )

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 50\text{mA}$		$BV_{CES}$	70	-	V
Collector-Emitter Leakage Current	$V_{CE} = 32\text{V}$		$I_{CES}$	-	10	mA
Thermal Resistance	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	$R_{TH(JC)}$	-	0.5	°C/W
Input Power	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	$P_{IN}$	-	16	W
Power Gain	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	$G_P$	8.0	-	dB
Collector Efficiency	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	$\eta_C$	52	-	%
Input Return Loss	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	RL	-	-9	dB
Load Mismatch Tolerance	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 32\text{V}$ , $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	VSWR-S	-	1.5:1	-

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## Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.1	14.9	100	8.26	5.23	59.8	-12.4	S	P
1.2	12.8	100	8.92	4.79	65.3	-12.1	S	P
1.3	13.7	100	8.63	4.98	62.7	-10.8	S	P

## RF Test Fixture Impedance

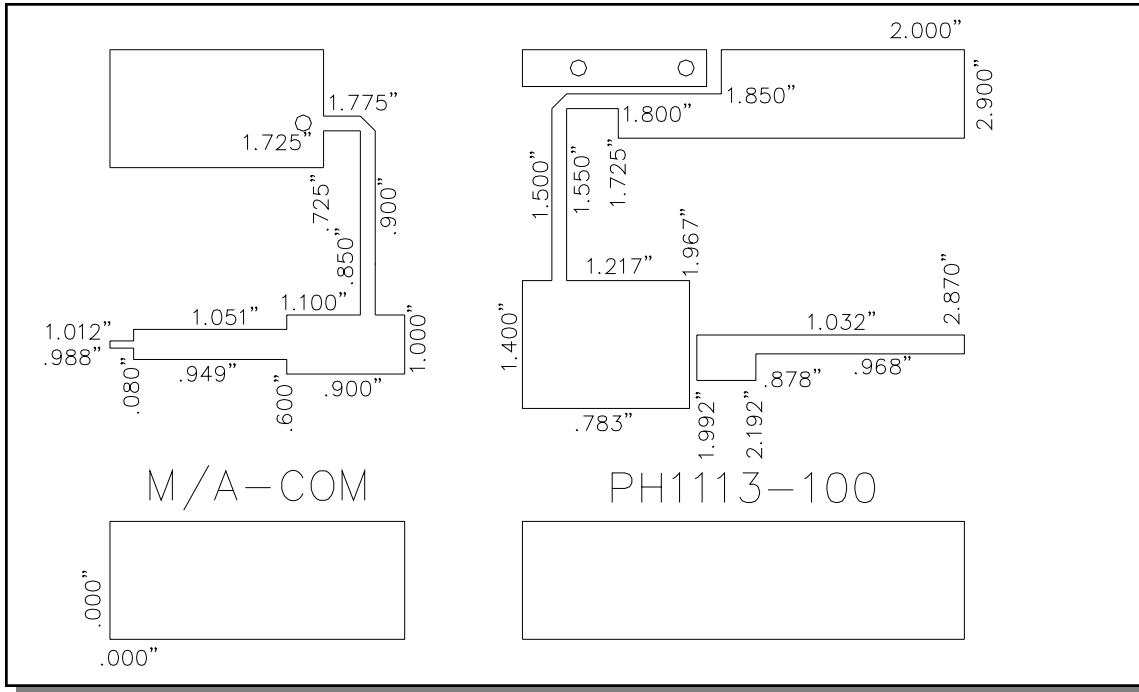
F (GHz)	Z <sub>IF</sub> ( $\Omega$ )	Z <sub>OF</sub> ( $\Omega$ )
1.1	5.8 - j3.4	3.0 - j1.7
1.2	5.6 - j1.8	3.0 - j1.5
1.3	5.9 - j0.4	2.8 - j1.3



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## Test Fixture Circuit Dimensions



## Test Fixture Assembly

